

SWITCHING DIODES

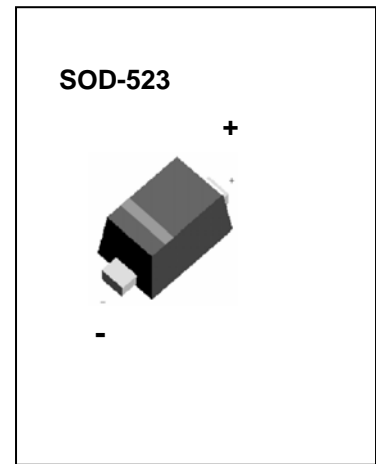
PRODUCT SUMMARY

SOD-523 Plastic-Encapsulate Diodes

FEATURES

Small surface mounting type
High switching speed

 **Pb-free; RoHS-compliant**



MARKING: 61

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

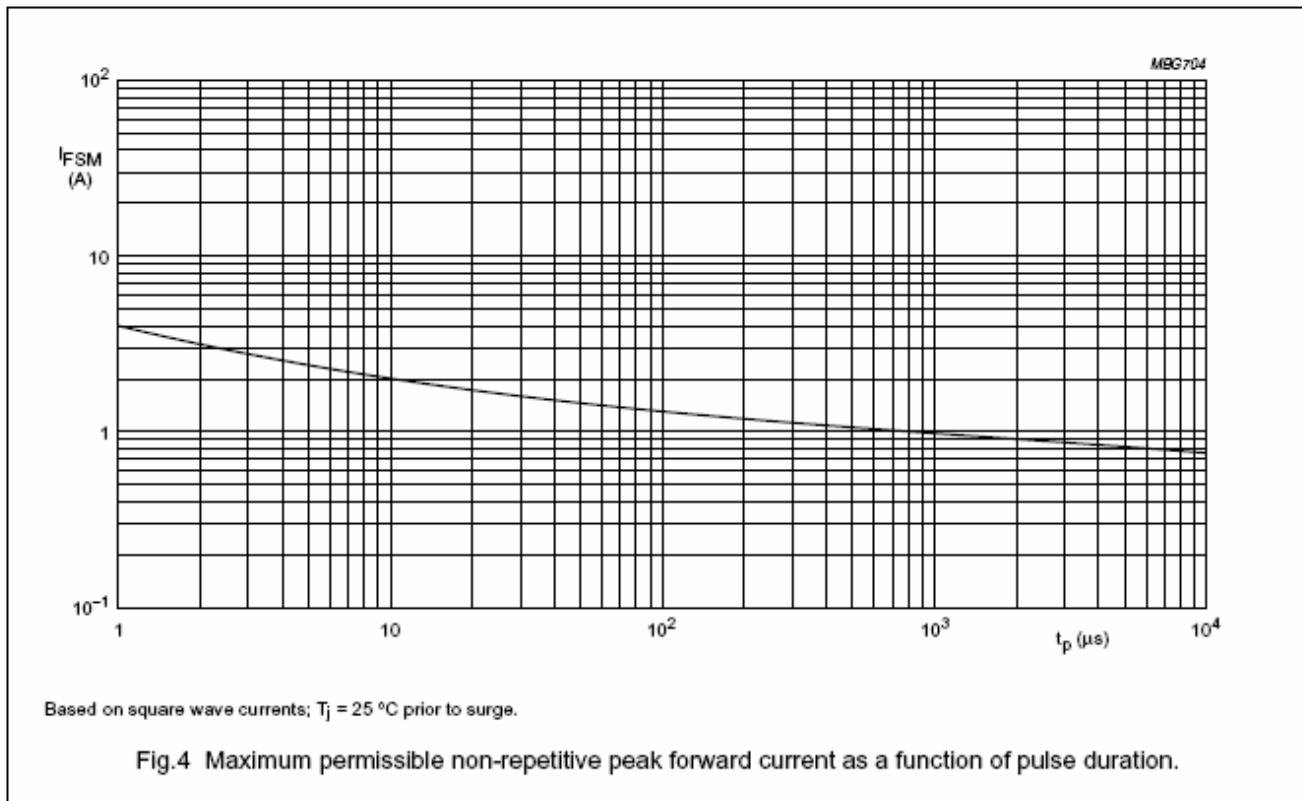
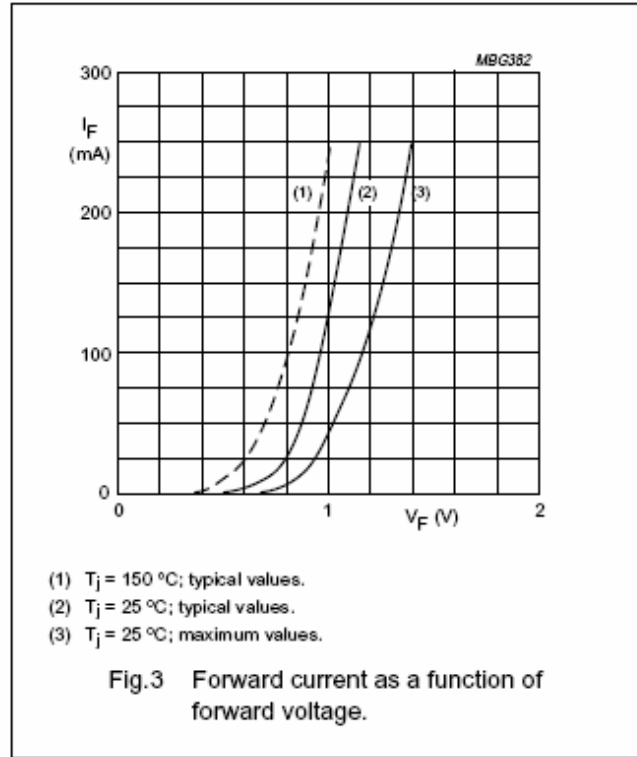
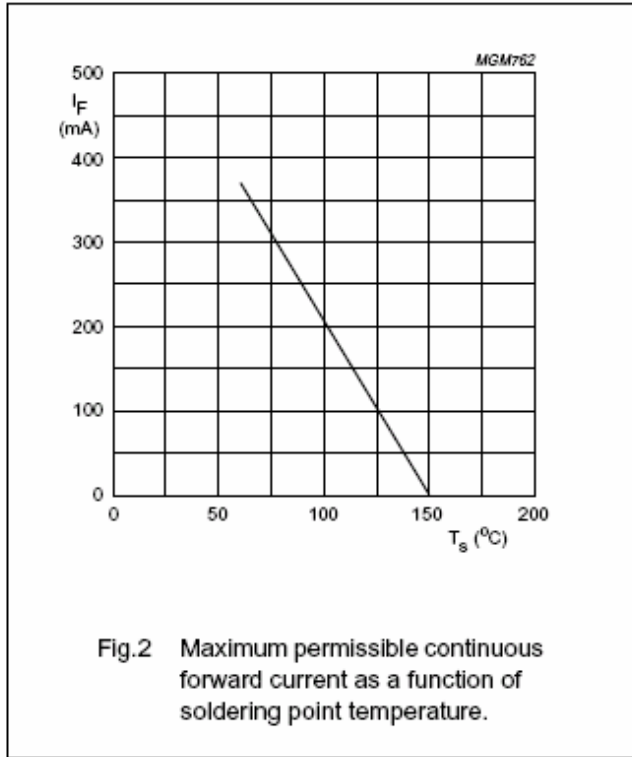
Single Diode @ $T_A=25^{\circ}\text{C}$

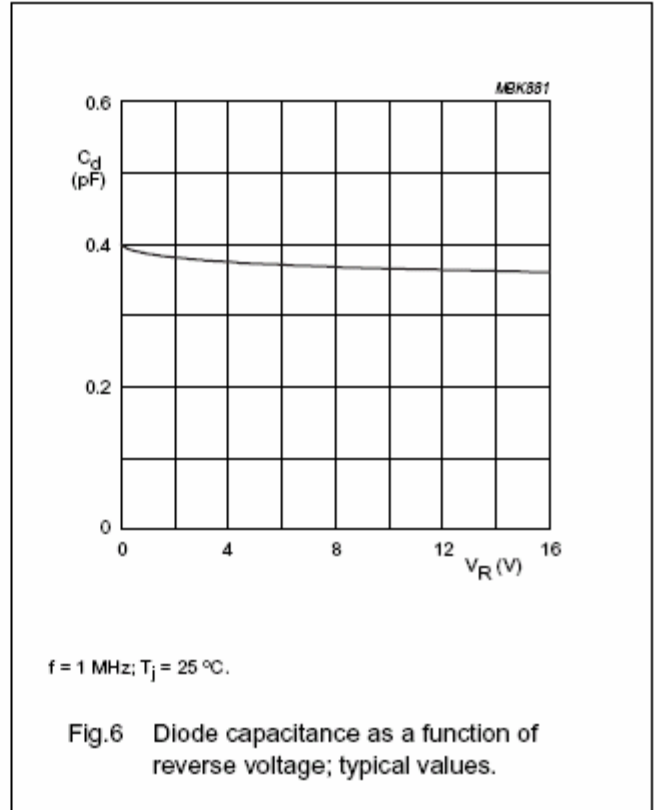
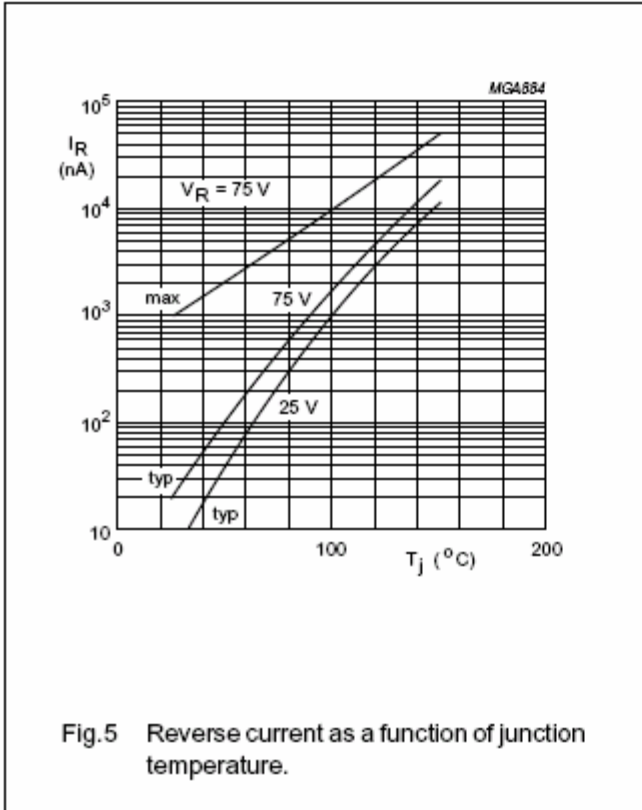
| Parameter | Symbol | Limits | Unit |
|----------------------------|-----------|----------|--------------------|
| DC reverse voltage | V_R | 75 | V |
| Mean rectifying current | I_O | 250 | mA |
| Peak forward surge current | I_{FSM} | 0.5 | A |
| Junction temperature | T_j | 150 | $^{\circ}\text{C}$ |
| Storage temperature | T_{stg} | -65~+150 | $^{\circ}\text{C}$ |

ELECTRICAL RATINGS @ $T_A=25^{\circ}\text{C}$

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|-------------------------------|----------|------|------|-----------------------------|---------------|--|
| Forward voltage | V_F | | | 0.715 0.855 1 1.25 | V | $I_F=1\text{mA}$ $I_F=10\text{mA}$ $I_F=50\text{mA}$ $I_F=150\text{mA}$ |
| Reverse current | I_R | | | 0.03 1 | μA | $V_R=25\text{V}$ $V_R=75\text{V}$ |
| Capacitance between terminals | C_T | | | 1 | pF | $V_R=0$, $f=1\text{MHZ}$ |
| Reverse recovery time | t_{rr} | | | 4 | ns | $I_F=10\text{mA}$, $R_L=100\Omega$ |

TYPICAL CHARACTERISTICS





Information furnished by Silicon Standard Corporation is believed to be accurate and reliable. However, Silicon Standard Corporation makes no guarantee or warranty, expressed or implied, as to the reliability, accuracy, timeliness or completeness of such information and assumes no responsibility for its use, or for infringement of any patent or other intellectual property rights of third parties that may result from its use. Silicon Standard reserves the right to make changes as it deems necessary to any products described herein for any reason, including without limitation enhancement in reliability, functionality or design. No license is granted, whether expressly or by implication, in relation to the use of any products described herein or to the use of any information provided herein, under any patent or other intellectual property rights of Silicon Standard Corporation or any third parties.